

Thyristor Module

MCMA140P1200TA

V_{RRM}	<i>=</i> 2x 1200 V			
I _{tav}	=	140 A		
Vτ	=	1.28 V		

Phase leg

Part number

MCMA140P1200TA



Backside: Isolated





Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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MCMA140P1200TA

Thyristo	or			Ratings			
Symbol	Definition	Conditions		min. t	yp.	max.	Unit
V _{RSM/DSM}	max. non-repetitive reverse/forwa	rd blocking voltage	$T_{VJ} = 25^{\circ}C$			1300	V
V _{RRM/DRM}	max. repetitive reverse/forward bi	ocking voltage	$T_{vJ} = 25^{\circ}C$			1200	V
I _{R/D}	reverse current, drain current	$V_{R/D} = 1200 V$	$T_{vJ} = 25^{\circ}C$			100	μA
		$V_{R/D} = 1200 V$	$T_{vJ} = 140^{\circ}C$			10	mA
VT	forward voltage drop	I _τ = 150 A	$T_{VJ} = 25^{\circ}C$			1.29	V
		$I_{T} = 300 \text{ A}$				1.63	V
		$I_{T} = 150 \text{ A}$	$T_{VJ} = 125^{\circ}C$			1.28	V
		$I_{T} = 300 \text{ A}$				1.70	V
ITAV	average forward current	$T_c = 85^{\circ}C$	T _{vJ} = 140°C			140	A
I _{T(RMS)}	RMS forward current	180° sine				220	Α
ν _{το}	threshold voltage		T _{vJ} = 140°C			0.85	V
r _T	slope resistance } for power in	oss calculation only				2.8	mΩ
\mathbf{R}_{thJC}	thermal resistance junction to cas	e				0.22	K/W
R _{thCH}	thermal resistance case to heatsi	nk		(0.2		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			520	W
I _{TSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			2.40	kA
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			2.59	kA
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 140$ °C			2.04	kA
		t = 8,3 ms; (60 Hz), sine	$V_{\text{B}} = 0 \text{ V}$			2.21	kA
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			28.8	kA²s
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			27.9	kA²s
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 140 ^{\circ}\text{C}$			20.8	kA²s
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			20.2	kA²s
C	junction capacitance	$V_R = 400 V$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		119		pF
P _{GM}	max. gate power dissipation	t _P = 30 μs	$T_c = 140^{\circ}C$			10	W
		t _P = 300 μs				5	W
P_{GAV}	average gate power dissipation					0.5	W
(di/dt) _{cr}	critical rate of rise of current	T _{vJ} = 140 °C; f = 50 Hz	repetitive, $I_T = 450 \text{ A}$			150	A/µs
		$t_{P} = 200 \mu s; di_{G}/dt = 0.45 A$	/μs;				
		$I_{G} = 0.45 \text{ A}; \text{ V } = \frac{2}{3} \text{ V}_{DRM}$	non-repet., $I_{T} = 150 \text{ A}$			500	A/µs
(dv/dt) _{cr}	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{vJ} = 140^{\circ}C$			1000	V/µs
		R _{GK} = ∞; method 1 (linear	voltage rise)				
V _{gt}	gate trigger voltage	$V_{D} = 6 V$	$T_{vJ} = 25^{\circ}C$			1.5	V
			$T_{vJ} = -40 ^{\circ}\text{C}$			1.6	V
I _{GT}	gate trigger current	$V_{D} = 6 V$	$T_{vJ} = 25^{\circ}C$			150	mA
			$T_{vJ} = -40 ^{\circ}\text{C}$			200	mA
V_{gd}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{vJ} = 140^{\circ}C$			0.2	V
	gate non-trigger current					10	mA
IL.	latching current	t _p = 10 μs	$T_{vJ} = 25 °C$			200	mA
		$I_{\rm G} = 0.45 \text{A}; di_{\rm G}/dt = 0.45 \text{A};$	5 A/μs				
I _H	holding current	$V_{D} = 6 V R_{GK} = \infty$	$T_{vJ} = 25 °C$			200	mA
t _{gd}	gate controlled delay time	$V_{D} = \frac{1}{2} V_{DRM}$	$T_{vJ} = 25 ^{\circ}C$			2	μs
		$I_{\rm G} = 0.45 \text{A}; di_{\rm G}/dt = 0.45 \text{A};$	5 A/μs				
t _q	turn-off time	$V_{R} = 100 \text{ V}; \text{ I}_{T} = 150 \text{ A}; \text{ V}$	$I = \frac{2}{3} V_{DRM} T_{VJ} = 125 \text{ °C}$		185		μs
		di/dt = 10 A/µs dv/dt =	20 V/ μ s t _p = 200 μ s				1 1 1

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MCMA140P1200TA

Package TO-240AA					Rating	S		
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					200	A
T _{vj}	virtual junction temperatur	e			-40		140	°C
T _{op}	operation temperature				-40		125	°C
T _{stg}	storage temperature				-40		125	°C
Weight						81		g
M _D	mounting torque				2.5		4	Nm
M _T	terminal torque				2.5		4	Nm
d _{Spp/App}	araanaaa diatanaa an aurfaaa Latriking diatanaa thrau		terminal to terminal	13.0	9.7			mm
$\mathbf{d}_{Spb/Apb}$	creepage distance on sun	ace striking distance through an	terminal to backside	16.0	16.0			mm
V _{ISOL}	isolation voltage	t = 1 second			4800			V
		t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1 \text{ mA}$		4000			V



Part description

M = Module C = Thyristor (SCR) M = Thyristor A = (up to 1800V) 140 = Current Rating [A] P = Phase leg 1200 = Reverse Voltage [V] TA = TO-240A-1B

TA = TO-240AA-1B

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCMA140P1200TA	MCMA140P1200TA	Box	36	512625

Similar Part	Package	Voltage class
MCMA140P1400TA	TO-240AA-1B	1400

Equiva	lent Circuits for	Simulation	* on die level	$T_{VJ} = 140^{\circ}C$
)[R	Thyristor		
V _{0 max}	threshold voltage	0.85		V
$\mathbf{R}_{0 \max}$	slope resistance *	1.6		mΩ

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Outlines TO-240AA



Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red Type ZY 200L (L = Left for pin pair 4/5) Type ZY 200R (R = Right for pin pair 6/7) UL 758, style 3751



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MCMA140P1200TA



Thyristor



2000

1600

1200

800

1000

100

1

10

t_{gd}

[µs] 10 0.01

 $T_{VJ} = 140^{\circ}C$

ITSM

[A]

50 Hz, 80% V

= 45°C

0.1

t [s]

 I_{TSM} : crest value, t: duration

Fig. 2 Surge overload current

1 imi

100

l_G [mA]

vn

1

= 25°C

1000

Fig. 1 Forward characteristics



Fig. 4 Gate voltage & gate current



Fig. 7b and ambient temperature

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